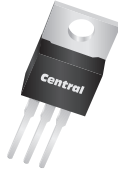


2N5294
2N5296
2N5298

NPN SILICON TRANSISTOR



TO-220 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N5294, 2N5296, and 2N5298 types are NPN silicon transistors manufactured by the epitaxial base process, and designed for applications that require power amplifier and medium speed switching capabilities.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Base Voltage	
Collector-Emitter Voltage	
Collector-Emitter Voltage ($R_{BE}=100\Omega$)	
Collector-Emitter Voltage	
Continuous Collector Current	
Continuous Base Current	
Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	
Thermal Resistance	

SYMBOL	2N5294	2N5296	2N5298	UNITS
V_{CBO}	80	60	80	V
V_{CEV}	80	60	80	V
V_{CER}	75	50	70	V
V_{CEO}	70	40	60	V
I_C		4.0		A
I_B		2.0		A
P_D		36		W
T_J, T_{stg}		-65 to +150		$^\circ\text{C}$
θ_{JA}		70		$^\circ\text{C/W}$
θ_{JC}		3.47		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N5294		2N5296		2N5298		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
I_{CEV}	$V_{CE}=35\text{V}, V_{EB}=1.5\text{V}$	-	-	-	2.0	-	-	mA
I_{CEV}	$V_{CE}=35\text{V}, V_{EB}=1.5\text{V}, T_C=150^\circ\text{C}$	-	-	-	5.0	-	-	mA
I_{CEV}	$V_{CE}=65\text{V}, V_{EB}=1.5\text{V}$	-	0.5	-	-	-	0.5	mA
I_{CEV}	$V_{CE}=65\text{V}, V_{EB}=1.5\text{V}, T_C=150^\circ\text{C}$	-	3.0	-	-	-	3.0	mA
I_{CER}	$V_{CE}=50\text{V}, R_{BE}=100\Omega$	-	0.5	-	-	-	0.5	mA
I_{CER}	$V_{CE}=50\text{V}, R_{BE}=100\Omega, T_C=150^\circ\text{C}$	-	2.0	-	-	-	2.0	mA
I_{EBO}	$V_{EB}=7.0\text{V}$	-	1.0	-	-	-	-	mA
I_{EBO}	$V_{EB}=5.0\text{V}$	-	-	-	1.0	-	1.0	mA
BV_{CEV}	$V_{BE}=1.5\text{V}, I_C=100\text{mA}$	80	-	60	-	80	-	V
BV_{CER}	$I_C=100\text{mA}, R_{BE}=100\Omega$	75	-	50	-	70	-	V
BV_{CEO}	$I_C=100\text{mA}$	70	-	40	-	60	-	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	1.0	-	-	-	-	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$	-	-	-	1.0	-	-	V
$V_{CE(SAT)}$	$I_C=1.5\text{A}, I_B=150\text{mA}$	-	-	-	-	-	1.0	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=500\text{mA}$	-	1.1	-	-	-	-	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=1.0\text{A}$	-	-	-	1.3	-	-	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=1.5\text{A}$	-	-	-	-	-	1.5	V

R1 (26-September 2012)

2N5294
2N5296
2N5298

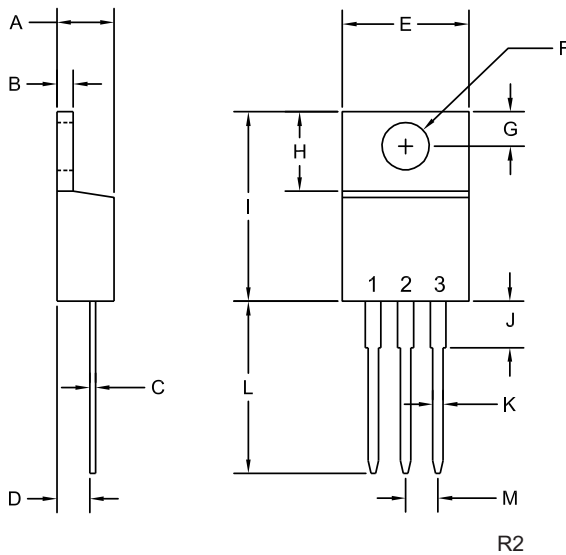
NPN SILICON TRANSISTOR



ELECTRICAL CHARACTERISTICS - Continued: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N5294		2N5296		2N5298		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
h_{FE}	$V_{CE}=4.0V, I_C=500mA$	30	120	-	-	-	-	
h_{FE}	$V_{CE}=4.0V, I_C=1.0A$	-	-	30	120	-	-	
h_{FE}	$V_{CE}=4.0V, I_C=1.5A$	-	-	-	-	20	80	
f_T	$V_{CE}=4.0V, I_C=200mA$	0.8	-	0.8	-	0.8	-	MHz
t_{on}	$V_{CC}=30V, I_C=500mA, I_B=50mA$	-	5.0	-	-	-	-	μs
t_{on}	$V_{CC}=30V, I_C=1.0A, I_B=100mA$	-	-	-	5.0	-	-	μs
t_{on}	$V_{CC}=30V, I_C=1.5A, I_B=150mA$	-	-	-	-	-	5.0	μs
t_{off}	$V_{CC}=30V, I_C=500mA, I_B=50mA$	-	15	-	-	-	-	μs
t_{off}	$V_{CC}=30V, I_C=1.0A, I_B=100mA$	-	-	-	15	-	-	μs
t_{off}	$V_{CC}=30V, I_C=1.5A, I_B=150mA$	-	-	-	-	-	15	μs

TO-220 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.170	0.190	4.31	4.82
B	0.045	0.055	1.15	1.39
C	0.013	0.026	0.33	0.65
D	0.083	0.107	2.10	2.72
E	0.394	0.417	10.01	10.60
F (DIA)	0.140	0.157	3.55	4.00
G	0.100	0.118	2.54	3.00
H	0.230	0.270	5.85	6.85
I	0.560	0.625	14.23	15.87
J	-	0.250	-	6.35
K	0.025	0.038	0.64	0.96
L	0.500	0.579	12.70	14.70
M	0.090	0.110	2.29	2.79

TO-220 (REV: R2)

LEAD CODE:

- 1) Base
- 2) Collector
- 3) Emitter
- Tab) Collector

MARKING: FULL PART NUMBER

R1 (26-September 2012)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: www.centrasemi.com/terms